

GENERAL DESCRIPTION

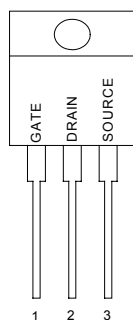
This high voltage MOSFET uses an advanced termination scheme to provide enhanced voltage-blocking capability without degrading performance over time. In addition, this advanced MOSFET is designed to withstand high energy in avalanche and commutation modes. The new energy efficient design also offers a drain-to-source diode with a fast recovery time. Designed for high voltage, high speed switching applications in power supplies, converters and PWM motor controls, these devices are particularly well suited for bridge circuits where diode speed and commutating safe operating areas are critical and offer additional and safety margin against unexpected voltage transients.

FEATURES

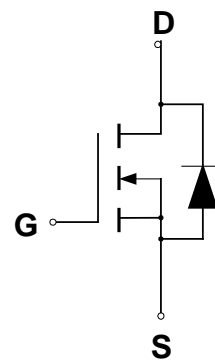
- ◆ Robust High Voltage Termination
- ◆ Avalanche Energy Specified
- ◆ Source-to-Drain Diode Recovery Time Comparable to a Discrete Fast Recovery Diode
- ◆ Diode is Characterized for Use in Bridge Circuits
- ◆ I_{DSS} and $V_{DS(on)}$ Specified at Elevated Temperature

PIN CONFIGURATION

TO-220/TO-220FP
Top View



SYMBOL



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS

| Rating | Symbol | Value | Unit |
|---|----------------|------------|------|
| Drain to Current - Continuous | I_D | 8.0 | A |
| - Pulsed | I_{DM} | 32 | |
| Gate-to-Source Voltage - Continue | V_{GS} | ± 20 | V |
| - Non-repetitive | V_{GSM} | ± 40 | V |
| Total Power Dissipation | P_D | | W |
| TO-220 | | 125 | |
| TO-220FP | | 40 | |
| Operating and Storage Temperature Range | T_J, T_{STG} | -55 to 150 | |
| Single Pulse Drain-to-Source Avalanche Energy - $T_J = 25$ ($V_{DD} = 100V, V_{GS} = 10V, I_L = 8A, L = 10mH, R_G = 25\Omega$) | E_{AS} | 320 | mJ |
| Thermal Resistance - Junction to Case | θ_{JC} | 1.0 | /W |
| - Junction to Ambient | θ_{JA} | 62.5 | |
| Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds | T_L | 260 | |

ORDERING INFORMATION

| Part Number | Package |
|----------------|---------------------|
| CMT08N50N220 | TO-220 |
| CMT08N50N220FP | TO-220 Full Package |

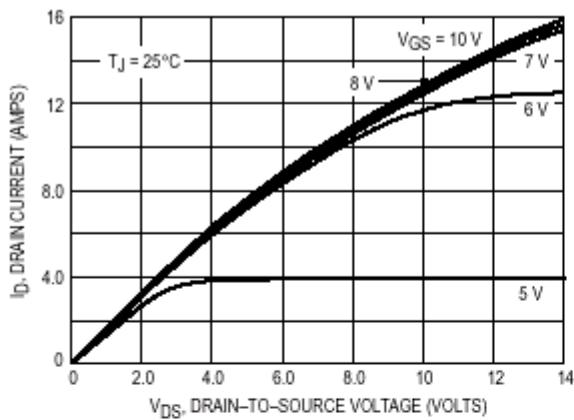
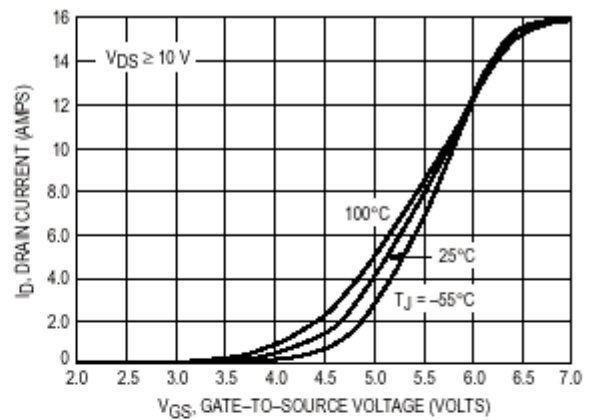
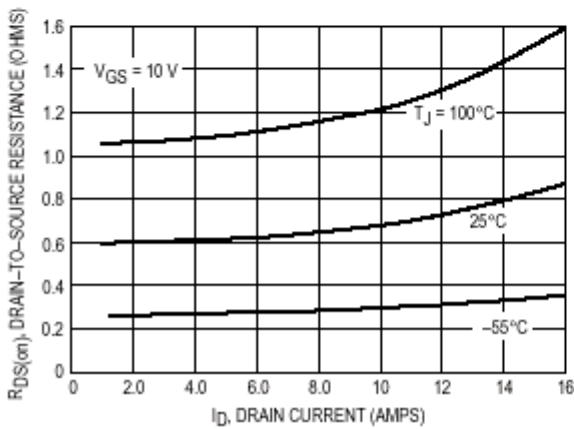
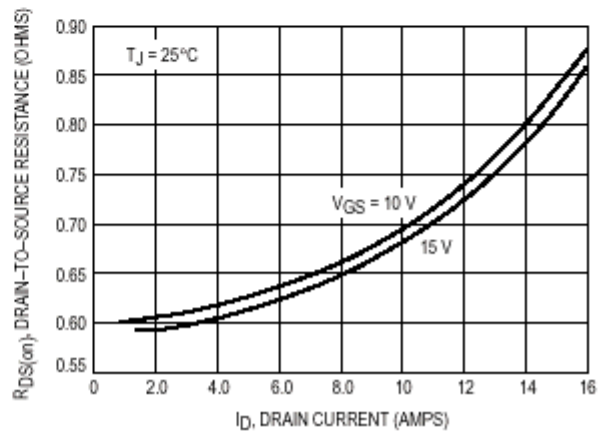
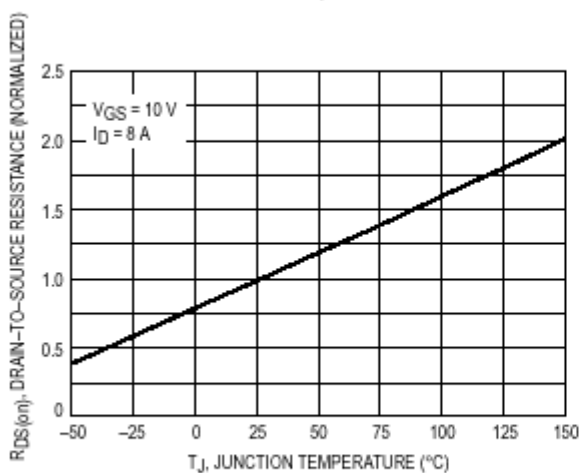
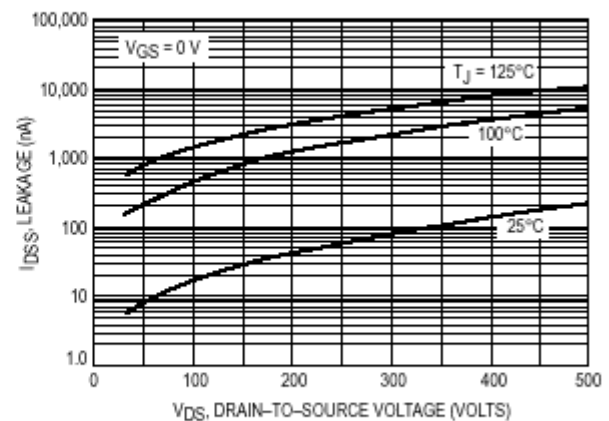
ELECTRICAL CHARACTERISTICS

Unless otherwise specified, $T_J = 25$.

| Characteristic | Symbol | CMT08N50 | | | Units |
|--|--|--------------|------|-----------|---------------|
| | | Min | Typ | Max | |
| Drain-Source Breakdown Voltage ($V_{GS} = 0\text{ V}$, $I_D = 250\ \mu\text{A}$) | $V_{(BR)DSS}$ | 500 | | | V |
| Drain-Source Leakage Current ($V_{DS} = 500\text{ V}$, $V_{GS} = 0\text{ V}$) ($V_{DS} = 400\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 125$) | I_{DSS} | | | 25 250 | μA |
| Gate-Source Leakage Current-Forward ($V_{gsf} = 20\text{ V}$, $V_{DS} = 0\text{ V}$) | I_{GSSF} | | | 100 | nA |
| Gate-Source Leakage Current-Reverse ($V_{gsr} = 20\text{ V}$, $V_{DS} = 0\text{ V}$) | I_{GSSR} | | | 100 | nA |
| Gate Threshold Voltage ($V_{DS} = V_{GS}$, $I_D = 250\ \mu\text{A}$) | $V_{GS(th)}$ | 2.0 | | 4.0 | V |
| Static Drain-Source On-Resistance ($V_{GS} = 10\text{ V}$, $I_D = 4.0\text{A}$) * | $R_{DS(on)}$ | | | 0.8 | Ω |
| Drain-Source On-Voltage ($V_{GS} = 10\text{ V}$) ($I_D = 8.0\text{ A}$) | $V_{DS(on)}$ | | 5.0 | 7.2 | V |
| Forward Transconductance ($V_{DS} = 50\text{ V}$, $I_D = 4.0\text{A}$) * | g_{FS} | 4.9 | | | mmhos |
| Input Capacitance | $(V_{DS} = 25\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1.0\text{ MHz}$) | C_{iss} | 1450 | 1680 | pF |
| Output Capacitance | | C_{oss} | 190 | 246 | pF |
| Reverse Transfer Capacitance | | C_{rss} | 45.4 | 144 | pF |
| Turn-On Delay Time | $(R_{Go} + C17n = 9.1\Omega)$ * | $t_{d(on)}$ | 15 | 50 | ns |
| Rise Time | | t_r | 33 | 72 | ns |
| Turn-Off Delay Time | | $t_{d(off)}$ | 40 | 150 | ns |
| Fall Time | | t_f | 32 | 60 | ns |
| Total Gate Charge | $(V_{DS} = 400\text{ V}$, $I_D = 8.0\text{ A}$, $V_{GS} = 10\text{ V})^*$ | Q_g | 40 | 64 | nC |
| Gate-Source Charge | | Q_{gs} | 8.0 | | nC |
| Gate-Drain Charge | | Q_{gd} | 17 | | nC |
| Internal Drain Inductance (Measured from the drain lead 0.25" from package to center of die) | L_D | | 4.5 | | nH |
| Internal Drain Inductance (Measured from the source lead 0.25" from package to source bond pad) | L_S | | 7.5 | | nH |
| SOURCE-DRAIN DIODE CHARACTERISTICS | | | | | |
| Forward On-Voltage(1) | $(I_S = 8.0\text{ A}$, $V_{GS} = 0\text{ V}$, $d_I/d_t = 100\text{A}/\mu\text{s}$) | V_{SD} | | 1.5 | V |
| Forward Turn-On Time | | t_{on} | ** | | ns |
| Reverse Recovery Time | | t_{rr} | 320 | | ns |

* Pulse Test: Pulse Width 300 μs , Duty Cycle 2%

** Negligible, Dominated by circuit inductance

TYPICAL ELECTRICAL CHARACTERISTICS

Figure 1. On-Region Characteristics

Figure 2. Transfer Characteristics

Figure 3. On-Resistance versus Drain Current and Temperature

Figure 4. On-Resistance versus Drain Current and Gate Voltage

Figure 5. On-Resistance Variation with Temperature

Figure 6. Drain-to-Source Leakage Current versus Voltage

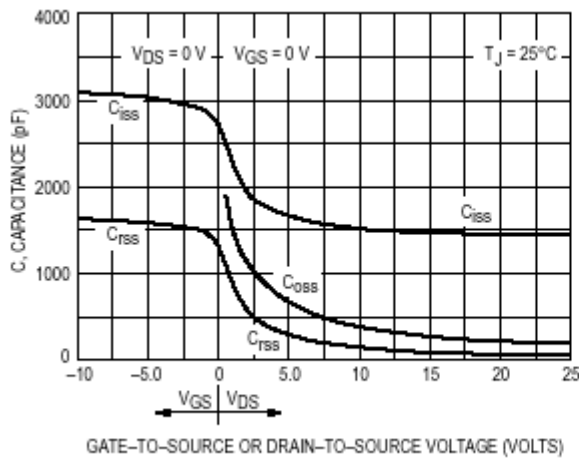


Figure 7. Capacitance Variation

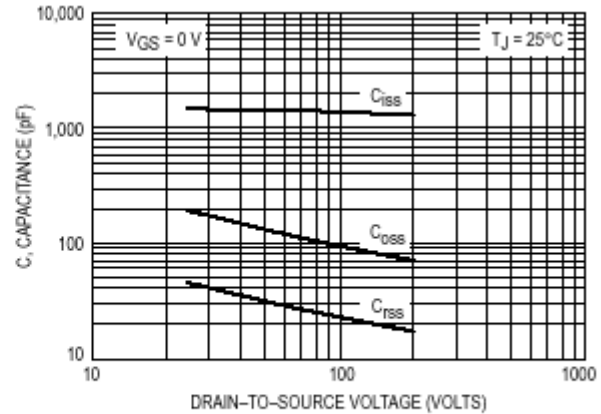


Figure 8. High Voltage Capacitance Variation

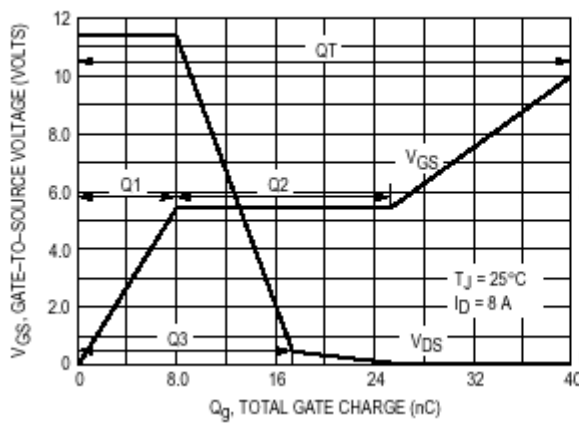


Figure 9. Gate-to-Source and Drain-to-Source Voltage versus Total Charge

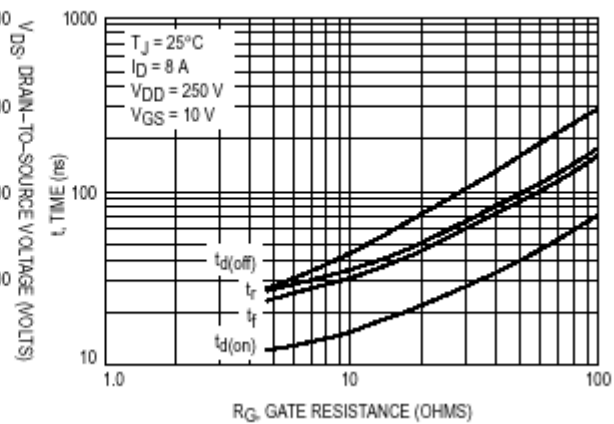


Figure 10. Resistive Switching Time Variation versus Gate Resistance

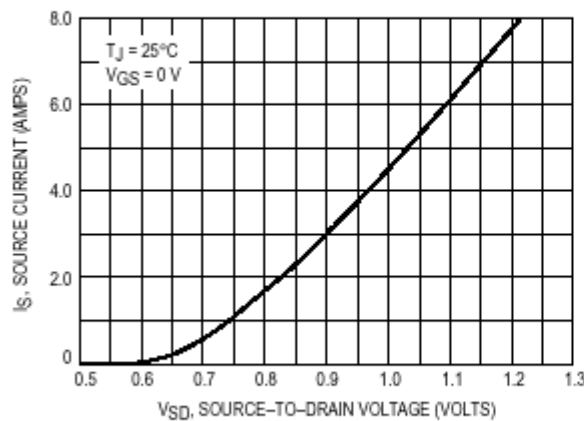


Figure 11. Diode Forward Voltage versus Current

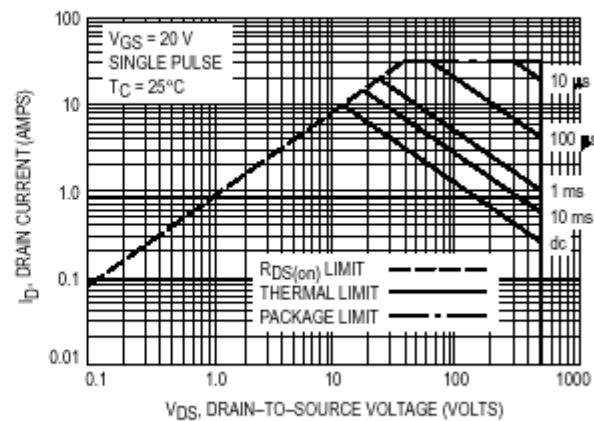


Figure 12. Maximum Rated Forward Biased Safe Operating Area

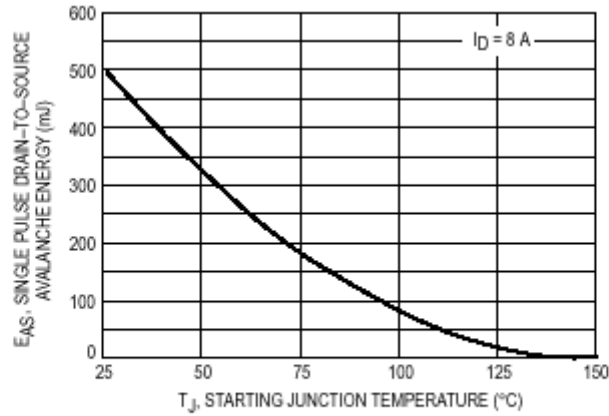


Figure 13. Maximum Avalanche Energy versus Starting Junction Temperature

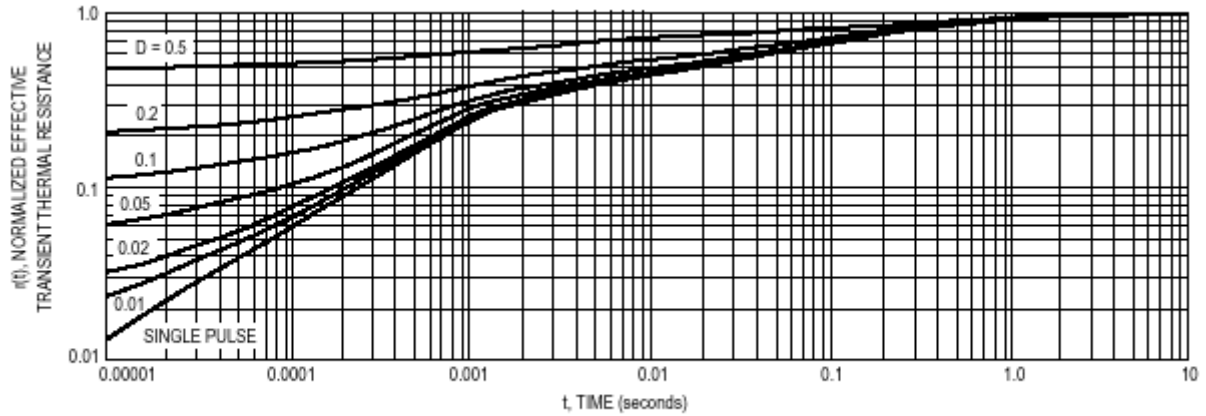
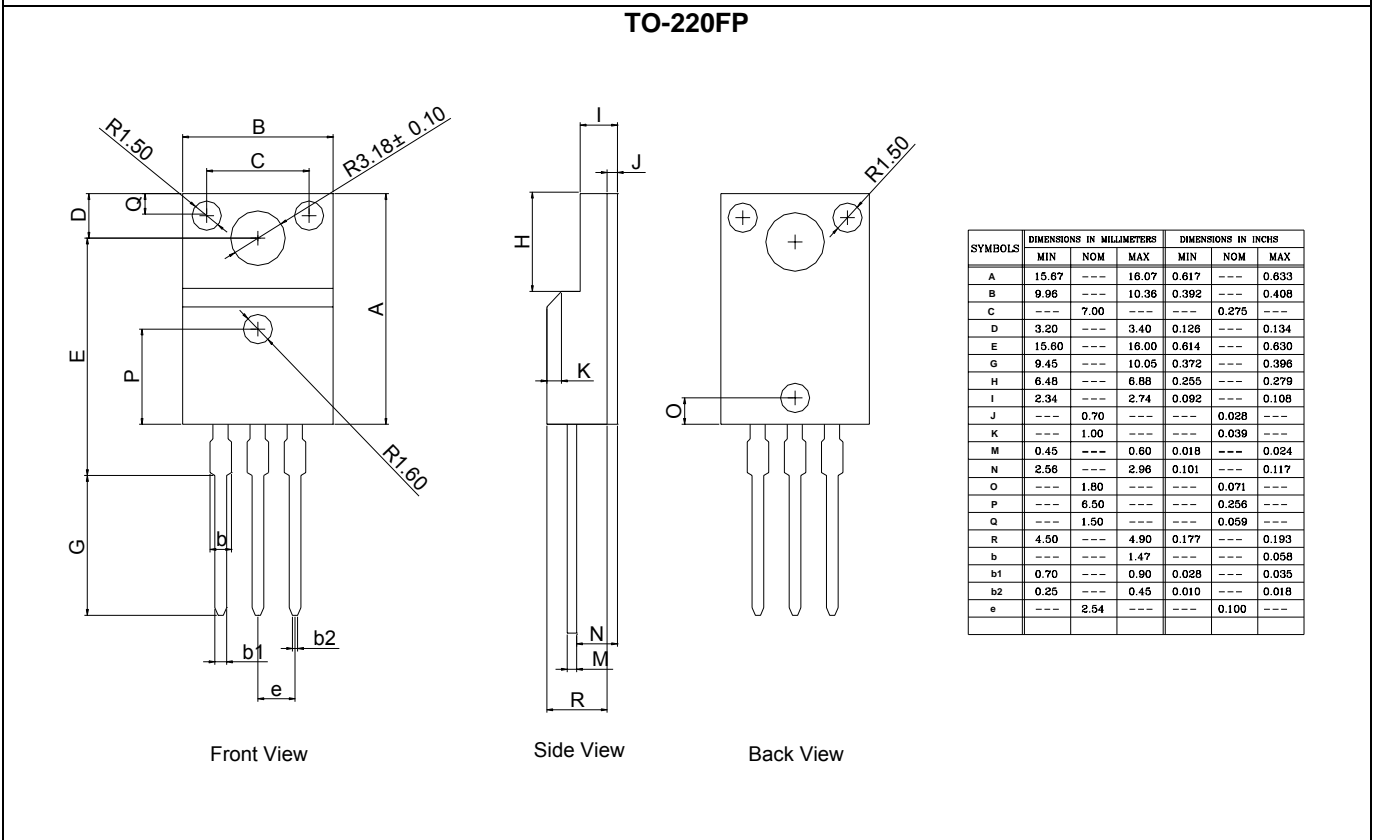
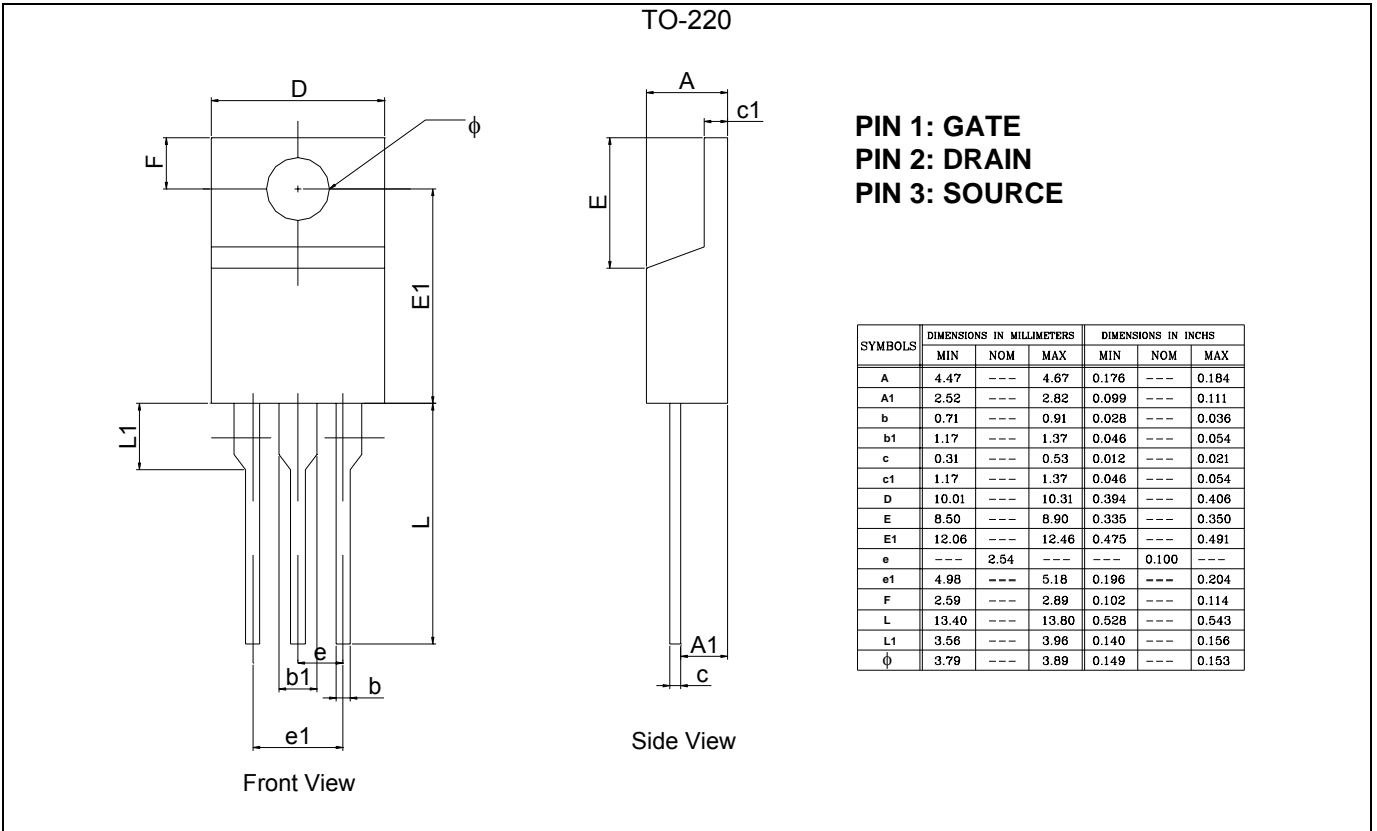


Figure 14. Thermal Response

PACKAGE DIMENSION



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